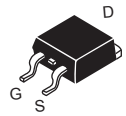
CEP11N65S/CEB11N65S
CEF11N65S

N-Channel Enhancement Mode Field Effect Transistor

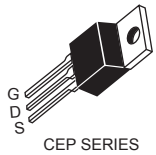
FEATURES

Type	V_{DSS}	$R_{DS(ON)}$	I_D	@V_{GS}
CEP11N65S	650V	0.42Ω	11A	10V
CEB11N65S	650V	0.42Ω	11A	10V
CEF11N65S	650V	0.42Ω	11A [d]	10V

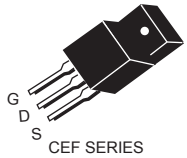
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handing capability.
- RoHS compliant.



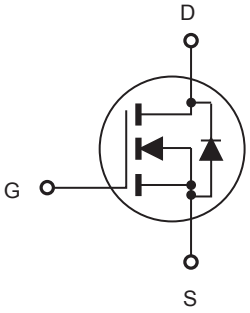
CEB SERIES
TO-263(DD-PAK)



CEP SERIES
TO-220



CEF SERIES
TO-220F



ABSOLUTE MAXIMUM RATINGS T_C = 25°C unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263	TO-220F	
Drain-Source Voltage	V_{DS}	650		V
Gate-Source Voltage	V_{GS}	±20		V
Drain Current-Continuous @ T_C = 25℃	I_D	11	11 [d]	A
@ T_C = 100°C		7	7 [d]	A
Drain Current-Pulsed [a]	I_{DM} [e]	44	44 [d]	A
Maximum Power Dissipation @ T_C = 25°C	P_D	125	31.2	W
- Derate above 25°C		1	0.24	W/℃
Single Pulsed Avalanche Energy [h]	E_{AS}	210		mJ
Single Pulsed Avalanche Current [h]	I_{AS}	1.7		A
Operating and Store Temperature Range	T_J,T_{stg}	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1	4	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	65	°C/W

Electrical Characteristics T_C = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = 250μA	650			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 650V, V_{GS} = 0V			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	V_{GS} = 20V, V_{DS} = 0V			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	V_{GS} = -20V, V_{DS} = 0V			-100	nA
On Characteristics [b]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 250μA	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 5.5A		0.35	0.42	Ω
Dynamic Characteristics [c]						
Input Capacitance	C_{iss}	V_{DS} = 100V, V_{GS} = 0V, f = 1.0 MHz		700	1050	pF
Output Capacitance	C_{oss}			75	115	pF
Reverse Transfer Capacitance	C_{rss}			15	25	pF
Switching Characteristics [c]						
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 400V, I_D =4.8A, V_{GS} = 10V, R_{GEN} = 3.4Ω		23		ns
Turn-On Rise Time	t_r			9		ns
Turn-Off Delay Time	$t_{d(off)}$			46		ns
Turn-Off Fall Time	t_f			8		ns
Total Gate Charge	Q_g	V_{DS} = 480V, I_D = 4.8A, V_{GS} = 10V		19		nC
Gate-Source Charge	Q_{gs}			3		nC
Gate-Drain Charge	Q_{gd}			8		nC
Drain-Source Diode Characteristics and Maximun Ratings						
Drain-Source Diode Forward Current	I_S [f]				11	A
Drain-Source Diode Forward Voltage [b]	V_{SD}	V_{GS} = 0V, I_S = 5.5A [g]			1.2	V

Notes :
a.Repetitive Rating : Pulse width limited by maximum junction temperature .
b.Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2% .
c.Guaranteed by design, not subject to production testing.
d.Limited only by maximum temperature allowed .
e.Pulse width limited by safe operating area .
f.Full package $I_{S(max)}$ = 5.5A .
g.Full package V_{SD} test condition I_S = 5.5A .
h.L = 130mH, I_{AS} = 1.7A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25 C

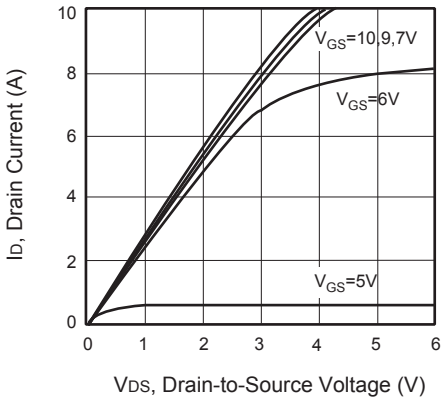


Figure 1. Output Characteristics

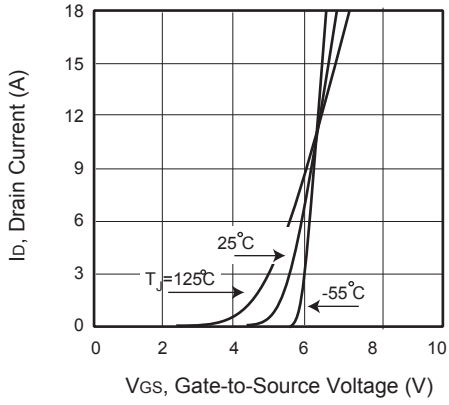


Figure 2. Transfer Characteristics

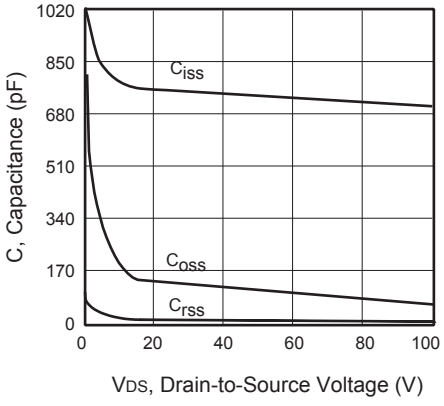


Figure 3. Capacitance

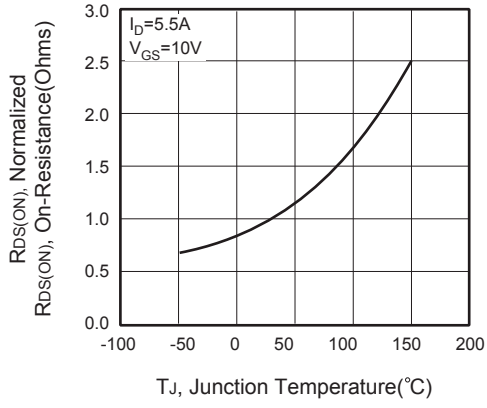


Figure 4. On-Resistance Variation with Temperature

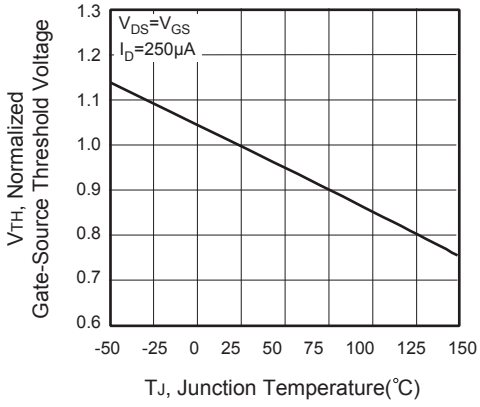


Figure 5. Gate Threshold Variation with Temperature

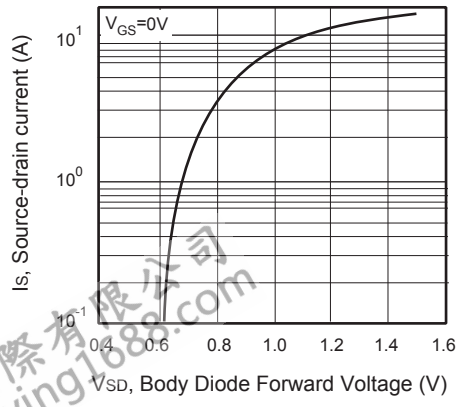


Figure 6. Body Diode Forward Voltage Variation with Source Current

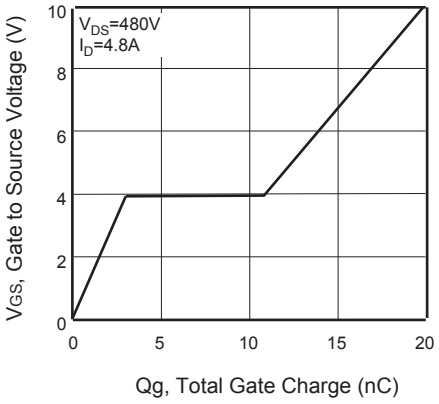


Figure 7. Gate Charge

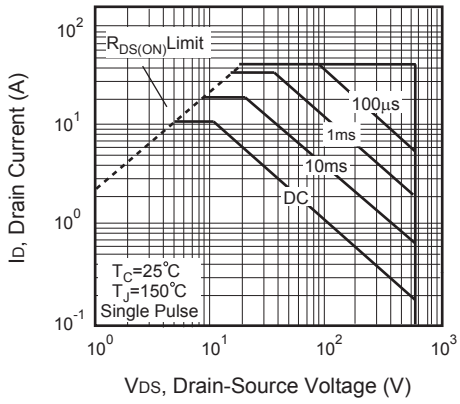


Figure 8. Maximum Safe Operating Area

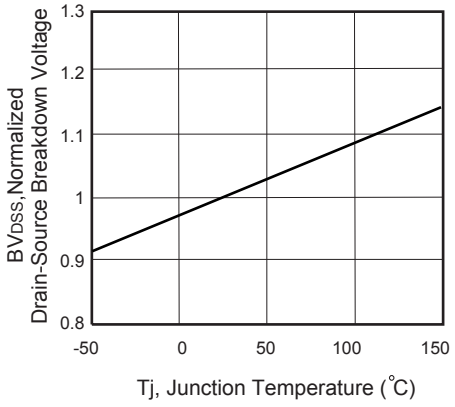


Figure 9. Breakdown Voltage Variation VS Temperature

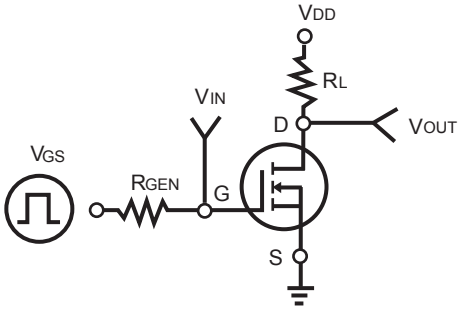


Figure 10. Switching Test Circuit

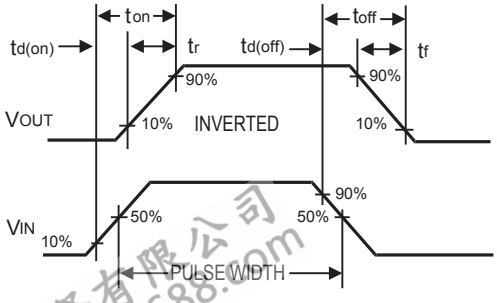


Figure 11. Switching Waveforms

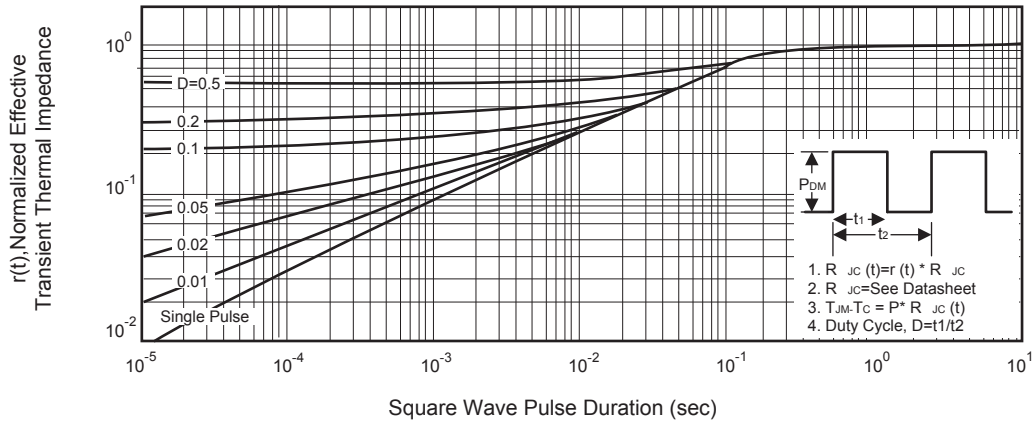
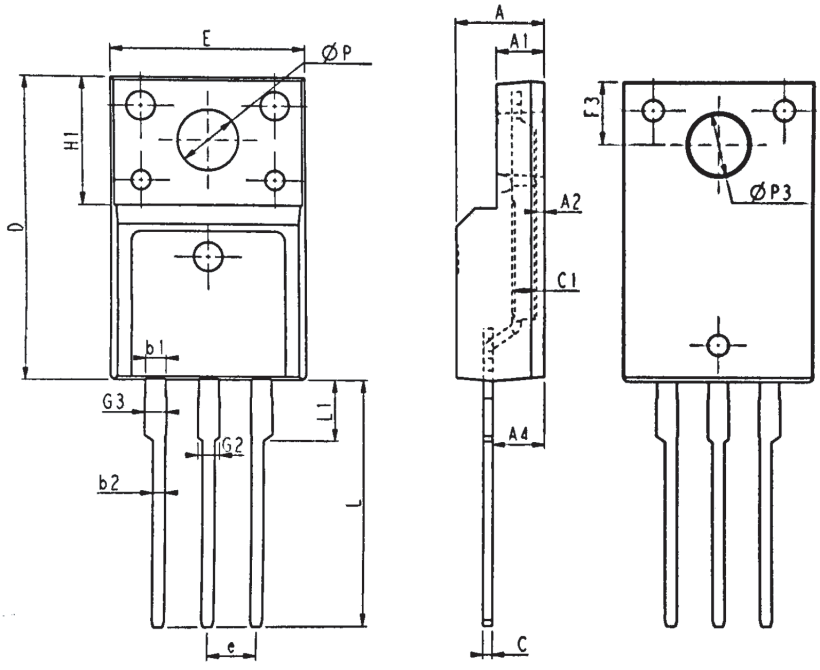


Figure 12. Normalized Thermal Transient Impedance Curve

TO-220F CEF11N65S 產品外觀尺寸圖 (Product Outline Dimension)



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
E	9.960	10.360	0.392	0.408
A	4.500	4.900	0.177	0.193
A1	2.340	2.740	0.092	0.108
A2	0.300	0.600	0.012	0.024
A4	2.560	2.960	0.101	0.117
c	0.450	0.650	0.018	0.026
c1	1.200	1.350	0.047	0.053
D	15.570	16.170	0.613	0.637
H1	0.67REF		0.026REF	
e	2.54BSC		0.100BSC	
L	12.680	13.280	0.499	0.523
L1	3.030	3.430	0.119	0.135
ØP	3.030	3.380	0.119	0.133
ØP3	3.150	3.650	0.124	0.144
F3	3.150	3.450	0.124	0.136
G2	1.000	1.300	0.039	0.051
G3	1.030	1.330	0.041	0.052
b1	0.950	1.250	0.037	0.049
b2	0.530	0.780	0.021	0.031